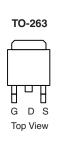
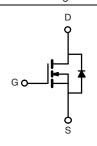


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# Automotive N-Channel 100 V (D-S) 175 °C MOSFET

| PRODUCT SUMMARY                                  |        |  |  |  |  |
|--|--------|--|--|--|--|
| V <sub>DS</sub> (V)                              | 100    |  |  |  |  |
| $R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$  | 0.0105 |  |  |  |  |
| $R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$ | 0.0120 |  |  |  |  |
| I <sub>D</sub> (A)                               | 100    |  |  |  |  |
| Configuration                                    | Single |  |  |  |  |





N-Channel MOSFET

#### **FEATURES**

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualified<sup>d</sup>
- 100 % R<sub>g</sub> and UIS Tested
- Material categorization:
   For definitions of compliance please see www.vishay.com/doc?99912





| ORDERING INFORMATION            |                  |
|---------------------------------|------------------|
| Package                         | TO-263           |
| Lead (Pb)-free and Halogen-free | SQM100N10-10-GE3 |

| <b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted) |                                     |                 |      |     |  |  |
|--|-------------------------------------|-----------------|------|-----|--|--|
| PARAMETER  | SYMBOL                              | LIMIT           | UNIT |     |  |  |
| Drain-Source Voltage   | $V_{DS}$                            | 100             | V    |     |  |  |
| Gate-Source Voltage  | $V_{GS}$                            | ± 20            | V    |     |  |  |
| Continuous Drain Current   | T <sub>C</sub> = 25 °C <sup>a</sup> | ,               | 100  |     |  |  |
| Continuous Drain Current   | T <sub>C</sub> = 125 °C             | I <sub>D</sub>  | 70   |     |  |  |
| Continuous Source Current (Diode Conduc  | I <sub>S</sub>                      | 100             | Α    |     |  |  |
| Pulsed Drain Current <sup>b</sup>  | I <sub>DM</sub>                     | 400             |      |     |  |  |
| Single Pulse Avalanche Current   |                                     | I <sub>AS</sub> | 75   |     |  |  |
| Single Pulse Avalanche Energy  | L = 0.1 mH                          | E <sub>AS</sub> | 280  | mJ  |  |  |
| Maximum Power Dissipation <sup>b</sup>   | T <sub>C</sub> = 25 °C              | D               | 375  | 14/ |  |  |
|  | T <sub>C</sub> = 125 °C             | $P_{D}$         | 125  | W   |  |  |
| Operating Junction and Storage Temperation                                       | T <sub>J</sub> , T <sub>stg</sub>   | - 55 to + 175   | °C   |     |  |  |

| THERMAL RESISTANCE RATINGS |                        |            |       |       |  |  |
|----------------------------|------------------------|------------|-------|-------|--|--|
| PARAMETER                  |                        | SYMBOL     | LIMIT | UNIT  |  |  |
| Junction-to-Ambient        | PCB Mount <sup>c</sup> | $R_{thJA}$ | 40    | °C/W  |  |  |
| Junction-to-Case (Drain)   |                        | $R_{thJC}$ | 0.4   | C/ VV |  |  |

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



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| PARAMETER                                     | SYMBOL                   | TES  | MIN.  | TYP. | MAX.   | UNIT   |    |  |
|---|--------------------------|--|---|------|--------|--------|----|--|
| Static  |                          |  |   |      |        |        |    |  |
| Drain-Source Breakdown Voltage                | V <sub>DS</sub>          | $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$  |   | 100  | -      | -      | V  |  |
| Gate-Source Threshold Voltage                 | V <sub>GS(th)</sub>      | V <sub>DS</sub> =  | = V <sub>GS</sub> , I <sub>D</sub> = 250 μA             | 1.5  | 2.0    | 2.5    | V  |  |
| Gate-Source Leakage                           | I <sub>GSS</sub>         | V <sub>DS</sub> =  | 0 V, V <sub>GS</sub> = ± 20 V                           | =.   | -      | ± 100  | nA |  |
|   |                          | V <sub>GS</sub> = 0 V  | V <sub>DS</sub> = 100 V                                 | -    | -      | 1      |    |  |
| Zero Gate Voltage Drain Current               | I <sub>DSS</sub>         | V <sub>GS</sub> = 0 V  | V <sub>DS</sub> = 100 V, T <sub>J</sub> = 125 °C        | -    | -      | 50     | μΑ |  |
|   |                          | V <sub>GS</sub> = 0 V  | V <sub>DS</sub> = 100 V, T <sub>J</sub> = 175 °C        | -    | -      | 500    | 1  |  |
| On-State Drain Current <sup>a</sup>           | I <sub>D(on)</sub>       | V <sub>GS</sub> = 10 V   | $V_{DS} \ge 5 V$  | 120  | -      | -      | Α  |  |
|   |                          | V <sub>GS</sub> = 10 V   | I <sub>D</sub> = 30 A                                   | -    | 0.0070 | 0.0105 | Ω  |  |
| Durin On the Oracle Business and              |                          | V <sub>GS</sub> = 10 V   | I <sub>D</sub> = 30 A, T <sub>J</sub> = 125 °C          | -    | -      | 0.0200 |    |  |
| Drain-Source On-State Resistance <sup>a</sup> | R <sub>DS(on)</sub>      | V <sub>GS</sub> = 10 V   | I <sub>D</sub> = 30 A, T <sub>J</sub> = 175 °C          | -    | -      | 0.0260 |    |  |
|   |                          | V <sub>GS</sub> = 4.5 V  | I <sub>D</sub> = 20 A                                   | -    | 0.0080 | 0.0120 |    |  |
| Forward Transconductanceb                     | 9 <sub>fs</sub>          | V <sub>DS</sub> = 15 V, I <sub>D</sub> = 30 A  |   | -    | 115    | -      | S  |  |
| Dynamic <sup>b</sup>                          |                          |  |   |      | •      |        | ,  |  |
| Input Capacitance                             | C <sub>iss</sub>         |  | V <sub>GS</sub> = 0 V V <sub>DS</sub> = 25 V, f = 1 MHz |      | 6440   | 8050   | pF |  |
| Output Capacitance                            | C <sub>oss</sub>         | $V_{GS} = 0 V$   |   |      | 655    | 820    |    |  |
| Reverse Transfer Capacitance                  | C <sub>rss</sub>         | 1  |   | -    | 315    | 395    | 1  |  |
| Total Gate Charge <sup>c</sup>                | $Q_g$                    |  |   | -    | 122    | 185    | nC |  |
| Gate-Source Charge <sup>c</sup>               | Q <sub>gs</sub>          | V <sub>GS</sub> = 10 V   | $V_{DS} = 50 \text{ V}, I_D = 85 \text{ A}$             | -    | 23     | -      |    |  |
| Gate-Drain Charge <sup>c</sup>                | $Q_{gd}$                 | 1  | 1 1 1   |      | 28     | -      |    |  |
| Gate Resistance                               | $R_g$                    |  | f = 1 MHz   |      | 1.41   | 2.30   | Ω  |  |
| Turn-On Delay Time <sup>c</sup>               | t <sub>d(on)</sub>       |  |   | -    | 13     | 20     |    |  |
| Rise Time <sup>c</sup>                        | t <sub>r</sub>           | $V_{DD} = 50 \text{ V}, \text{ R}_{L} = 0.6 \Omega$ $I_{D} \cong 85 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_{g} = 2.5 \Omega$ |   | -    | 14     | 21     | ns |  |
| Turn-Off Delay Time <sup>c</sup>              | t <sub>d(off)</sub>      |  |   | -    | 44     | 66     |    |  |
| Fall Time <sup>c</sup>                        | t <sub>f</sub>           |  |   | -    | 10     | 15     |    |  |
| Source-Drain Diode Ratings and Chara          | acteristics <sup>b</sup> |  |   |      |        |        |    |  |
| Pulsed Current <sup>a</sup>                   | I <sub>SM</sub>          |  |   | -    | -      | 400    | Α  |  |
| Forward Voltage                               | V <sub>SD</sub>          | I <sub>F</sub> = 85 A, V <sub>GS</sub> = 0 V   |   | -    | 0.9    | 1.5    | V  |  |
|   |                          |  |   |      |        |        |    |  |

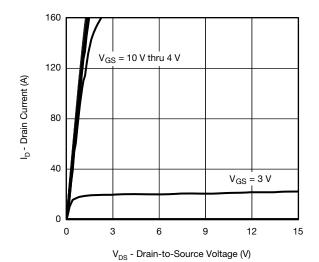
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,\,duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

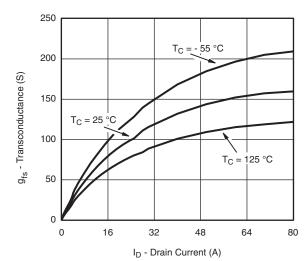
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



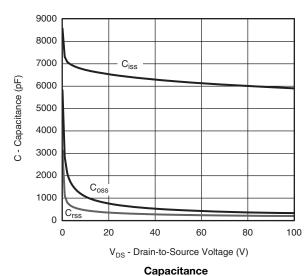
# **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

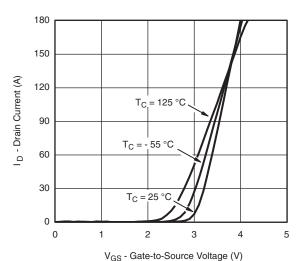


#### **Output Characteristics**



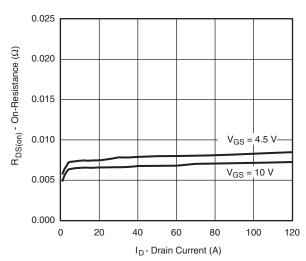
#### Transconductance



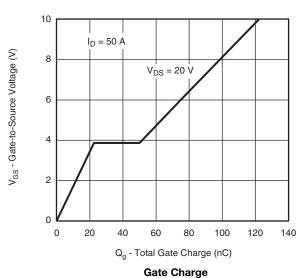


vas dato to course voltage (v)

#### **Transfer Characteristics**



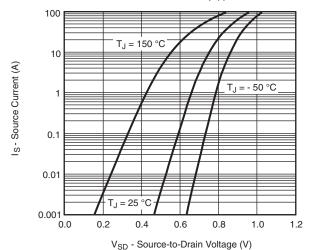
#### On-Resistance vs. Drain Current

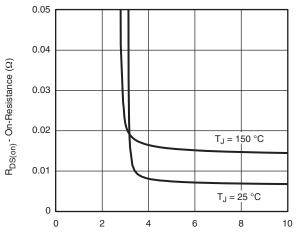


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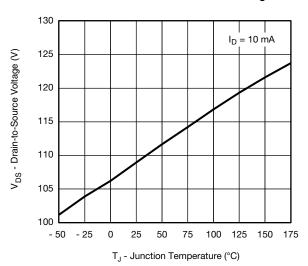
### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



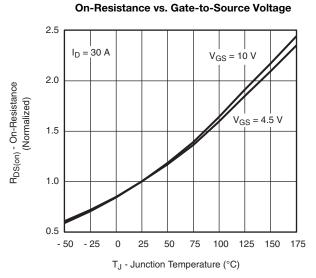


 $V_{\text{GS}}$  - Gate-to-Source Voltage (V)

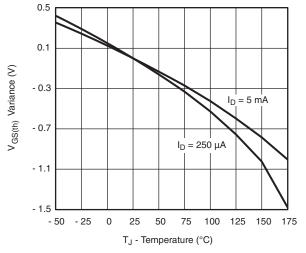
#### **Source Drain Diode Forward Voltage**



Breakdown Voltage vs. Junction Temperature

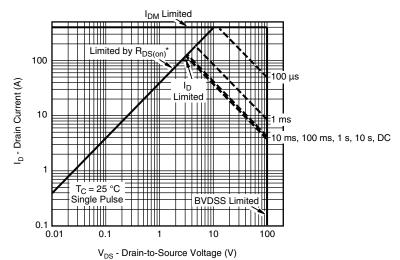


Normalized On-Resistance vs. Junction Temperature



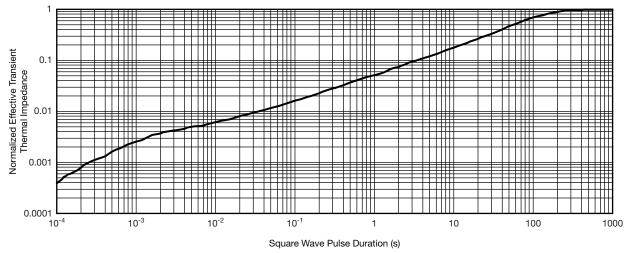
Threshold Voltage Variance vs. Junction Temperature

# **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



\*  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

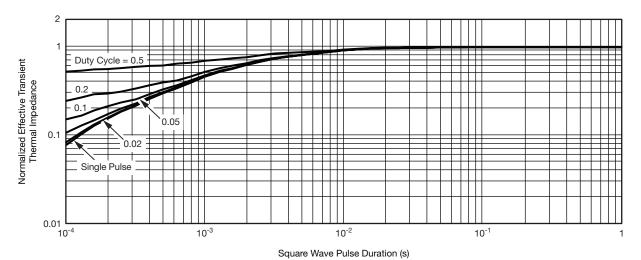
### Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



# THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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# TO-263 (D<sup>2</sup>PAK): 3-LEAD









DETAIL A (ROTATED 90°)



| ⋝: | ,  | <br> | b—<br>b1– |     | ļ          | ļ |
|----|----|------|-----------|-----|------------|---|
| 2: | П  |      |           |     | 5          | ပ |
|    | SE | СТ   | ION       | ΙΔ. | - 1<br>- Δ | Ŧ |

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. \*: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6 This feature is for thick lead.

|                                 |            | INCHES    |       | MILLIMETERS |        |  |
|---------------------------------|------------|-----------|-------|-------------|--------|--|
|                                 | DIM.       | MIN.      | MAX.  | MIN.        | MAX.   |  |
| Α                               |            | 0.160     | 0.190 | 4.064       | 4.826  |  |
|                                 | b          | 0.020     | 0.039 | 0.508       | 0.990  |  |
|                                 | b1         | 0.020     | 0.035 | 0.508       | 0.889  |  |
|                                 | b2         | 0.045     | 0.055 | 1.143       | 1.397  |  |
| c*                              | Thin lead  | 0.013     | 0.018 | 0.330       | 0.457  |  |
|                                 | Thick lead | 0.023     | 0.028 | 0.584       | 0.711  |  |
| c1                              | Thin lead  | 0.013     | 0.017 | 0.330       | 0.431  |  |
| CI                              | Thick lead | 0.023     | 0.027 | 0.584       | 0.685  |  |
|                                 | c2         | 0.045     | 0.055 | 1.143       | 1.397  |  |
|                                 | D          | 0.340     | 0.380 | 8.636       | 9.652  |  |
|                                 | D1         | 0.220     | 0.240 | 5.588       | 6.096  |  |
| D2                              |            | 0.038     | 0.042 | 0.965       | 1.067  |  |
| D3                              |            | 0.045     | 0.055 | 1.143       | 1.397  |  |
| D4                              |            | 0.044     | 0.052 | 1.118       | 1.321  |  |
|                                 | Е          | 0.380     | 0.410 | 9.652       | 10.414 |  |
|                                 | E1         | 0.245     | -     | 6.223       | -      |  |
|                                 | E2         | 0.355     | 0.375 | 9.017       | 9.525  |  |
|                                 | E3         | 0.072     | 0.078 | 1.829       | 1.981  |  |
|                                 | е          | 0.100     | BSC   | 2.54 BSC    |        |  |
|                                 | K          | 0.045     | 0.055 | 1.143       | 1.397  |  |
|                                 | L          | 0.575     | 0.625 | 14.605      | 15.875 |  |
| L1                              |            | 0.090     | 0.110 | 2.286       | 2.794  |  |
| L2                              |            | 0.040     | 0.055 | 1.016       | 1.397  |  |
| L3                              |            | 0.050     | 0.070 | 1.270       | 1.778  |  |
|                                 | L4         | 0.010 BSC |       | 0.254 BSC   |        |  |
|                                 | М          | -         | 0.002 | -           | 0.050  |  |
| ECN: T13-0707-Rev. K, 30-Sep-13 |            |           |       |             |        |  |

DWG: 5843





# RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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